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DERWENT-WEEK: 200203
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TITLE: Dry etching of oxide film involves using
fluorocarbon gas containing
sulfur

INVENTOR: AHN, T H; CHOO, C U ; JUNG, S S ; KANG, C J

PATENT-ASSIGNEE: SAMSUNG ELECTRONICS CO LTD[SMSU]

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PATENT-FAMILY:

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APPLICATION-DATA:

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KR2001010568A	N/A	1999KR-0029535
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INT-CL (IPC): C23C016/00

ABSTRACTED-PUB-NO: KR2001010568A

BASIC-ABSTRACT: NOVELTY - Provided is a method of dry
etching of an oxide film,
which increases etching selection ratio to a nitride film
by side product
non-volatile and unstable and prevents global warming
because decomposition is
easy in the atmosphere by using fluorocarbon gas containing
sulfur as an
etching gas.

DETAILED DESCRIPTION - The method of dry etching of the
oxide film using the
nitride film as etching a barrier layer is characterized by
providing the

etching gas composed of fluorocarbon gas containing sulfur
that is C4F8S,
C3F6S, C3F6S2, hydrofluorocarbon (HFC) containing sulfur or
mixture thereof, and
the etching gas can contain further oxygen, gas contained
oxygen, a CxFy (x =
1-6 and y = 2-12) gas, a CxHyFz (x = 1-6, y = 1-4 and z =
2-10) gas, an inert
gas or mixture thereof.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS:

DRY ETCH OXIDE FILM FLUOROCARBON GAS CONTAIN

DERWENT-CLASS: E16 L03

CPI-CODES: E10-F01; E10-H04A3; E31-F04; L04-C07B;

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